

# **MMBD4148**

# High-speed switching diode Rev. 01 — 4 June 2009

**Product data sheet** 

### **Product profile**

### 1.1 General description

High-speed switching diode, encapsulated in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

#### 1.2 Features

- High switching speed:  $t_{rr} \le 4$  ns
- Low leakage current
- Repetitive peak reverse voltage:  $V_{RRM} \le 75 \text{ V}$
- Low capacitance
- Reverse voltage: V<sub>R</sub> ≤ 75 V
- Small SMD plastic package

### 1.3 Applications

- High-speed switching
- General-purpose switching

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{R}$	reverse voltage		-	-	75	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 75 V	-	-	0.5	μΑ
t <sub>rr</sub>	reverse recovery time		<u>[1]</u> -	-	4	ns

<sup>[1]</sup> When switched from  $I_F$  = 10 mA to  $I_R$  = 10 mA;  $R_L$  = 100  $\Omega$ ; measured at  $I_R$  = 1 mA.

#### **Pinning information** 2.

Table 2. **Pinning** 

	3		
Pin	Description	Simplified outline	Graphic symbol
1	anode		
2	not connected		3
3	cathode	1 2	1



### 3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
MMBD4148	-	plastic surface-mounted package; 3 leads	SOT23		

### 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
MMBD4148	A6*

[1] \* = -: made in Hong Kong

\* = p: made in Hong Kong

\* = t: made in Malaysia

\* = W: made in China

### 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	75	V
$V_{R}$	reverse voltage		-	75	V
I <sub>F</sub>	forward current		<u>[1]</u> _	215	mA
I <sub>FRM</sub>	repetitive peak forward current	$t_p \leq 0.5~\mu\text{s}; \\ \delta \leq 0.25$	-	500	mA
I <sub>FSM</sub>	non-repetitive peak forward current	square wave	<u>[2]</u>		
		$t_p = 1 \mu s$	-	4	Α
		$t_p = 1 \text{ ms}$	-	1	Α
		$t_p = 1 s$	-	0.5	Α
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u> _	250	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup>  $T_j = 25$  °C prior to surge.

### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] _	-	500	K/W
$R_{th(j-t)}$	thermal resistance from junction to tie-point		-	-	330	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

### 7. Characteristics

Table 7. Characteristics

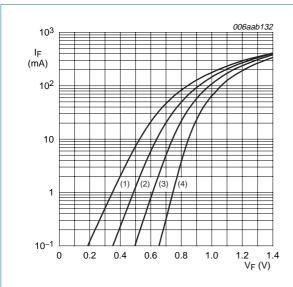
 $T_{amb}$  = 25 °C unless otherwise specified.

	•					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{F}$	forward voltage		<u>[1]</u>			
		$I_F = 1 \text{ mA}$	-	-	715	mV
		$I_F = 10 \text{ mA}$	-	-	855	mV
		$I_F = 50 \text{ mA}$	-	-	1	V
		I <sub>F</sub> = 150 mA	-	-	1.25	V
I <sub>R</sub> revers	reverse current	V <sub>R</sub> = 25 V	-	-	30	nA
		V <sub>R</sub> = 75 V	-	-	0.5	μΑ
		V <sub>R</sub> = 25 V; T <sub>j</sub> = 150 °C	-	-	30	μΑ
		V <sub>R</sub> = 75 V; T <sub>j</sub> = 150 °C	-	-	50	μΑ
$C_{d}$	diode capacitance	$f = 1 MHz; V_R = 0 V$	-	-	1.5	pF
t <sub>rr</sub>	reverse recovery time		[2] _	-	4	ns
$V_{FR}$	forward recovery voltage		[3] _	-	1.75	V

<sup>[1]</sup> Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

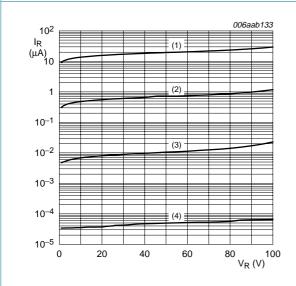
<sup>[2]</sup> When switched from  $I_F$  = 10 mA to  $I_R$  = 10 mA;  $R_L$  = 100  $\Omega$ ; measured at  $I_R$  = 1 mA.

<sup>[3]</sup> When switched from  $I_F = 10$  mA;  $t_r = 20$  ns.



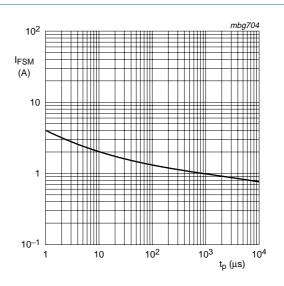
- (1)  $T_{amb} = 150 \, ^{\circ}C$
- (2)  $T_{amb} = 85 \, ^{\circ}C$
- (3)  $T_{amb} = 25 \, ^{\circ}C$
- (4)  $T_{amb} = -40 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



- (1)  $T_{amb} = 150 \, ^{\circ}C$
- (2)  $T_{amb} = 85 \, ^{\circ}C$
- (3)  $T_{amb} = 25 \, ^{\circ}C$
- (4)  $T_{amb} = -40 \, ^{\circ}C$

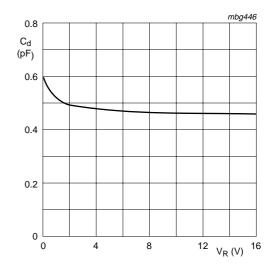
Fig 3. Reverse current as a function of reverse voltage; typical values



Based on square wave currents.

 $T_j = 25$  °C; prior to surge

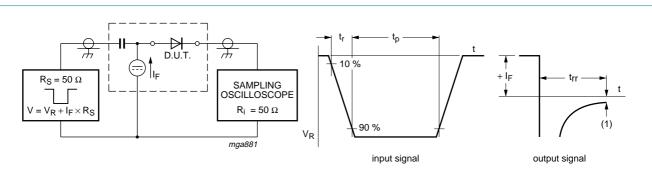
Fig 2. Non-repetitive peak forward current as a function of pulse duration; maximum values



 $f = 1 \text{ MHz}; T_{amb} = 25 \, ^{\circ}\text{C}$ 

Fig 4. Diode capacitance as a function of reverse voltage; typical values

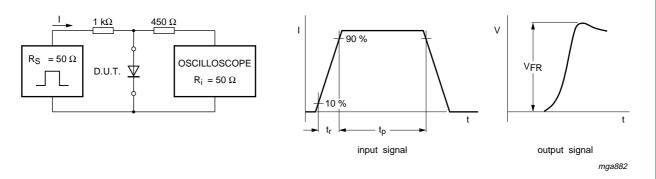
### 8. Test information



(1)  $I_R = 1 \text{ mA}$ 

Input signal: reverse pulse rise time  $t_r$  = 0.6 ns; reverse voltage pulse duration  $t_p$  = 100 ns; duty cycle  $\delta$  = 0.05 Oscilloscope: rise time  $t_r$  = 0.35 ns

Fig 5. Reverse recovery time test circuit and waveforms

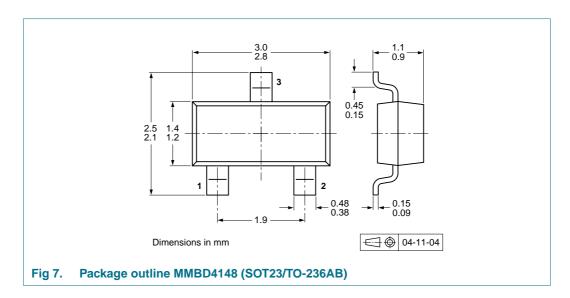


Input signal: forward pulse rise time  $t_r$  = 20 ns; forward current pulse duration  $t_p \ge 100$  ns; duty cycle  $\delta \le 0.005$ 

Fig 6. Forward recovery voltage test circuit and waveforms

**High-speed switching diode** 

### 9. Package outline



# 10. Packing information

Table 8. Packing methods

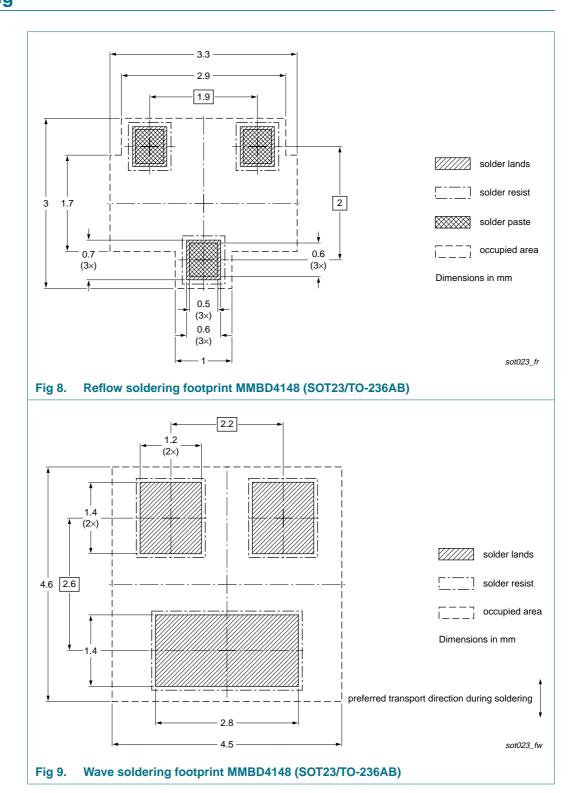
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
MMBD4148	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

[1] For further information and the availability of packing methods, see Section 14.

**High-speed switching diode** 

### 11. Soldering



**MMBD4148** 

High-speed switching diode

## 12. Revision history

### Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
MMBD4148_1	20090604	Product data sheet	-	-

#### High-speed switching diode

### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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### **High-speed switching diode**

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